## **VS-ST300C Series**

Vishay Semiconductors



### Phase Control Thyristors (Hockey PUK Version), 650 A



E-PUK (TO-200AB)

PRIMARY CHARACTERISTICS				
I <sub>T(AV)</sub>	650 A			
V <sub>DRM</sub> /V <sub>RRM</sub>	400 V, 800 V, 1200 V, 1600 V, 1800 V, 2000 V			
V <sub>TM</sub>	2.18 V			
I <sub>GT</sub>	100 mA			
TJ	-40 °C to +125 °C			
Package	E-PUK (TO-200AB)			
Circuit configuration	Single SCR			

### FEATURES

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case E-PUK (TO-200AB)
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### **TYPICAL APPLICATIONS**

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATING	S AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS	
1		650	A	
I <sub>T(AV)</sub>	T <sub>hs</sub>	55	°C	
1		1290	A	
IT(RMS)	T <sub>hs</sub>	25	°C	
1	50 Hz	8000	•	
ITSM	60 Hz	8380	- A	
l <sup>2</sup> t	50 Hz	320	- kA <sup>2</sup> s	
1-1	60 Hz	292	KA-S	
V <sub>DRM</sub> /V <sub>RRM</sub>		400 to 2000	V	
t <sub>q</sub>	Typical	100	μs	
TJ		-40 to 125	°C	

### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS						
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM}$ MAXIMUM AT T <sub>J</sub> = T <sub>J</sub> MAXIMUM mA		
	04	400	500			
	08	800	900			
VS-ST300CC	12	1200	1300	50		
10 0100000	16	1600	1700	00		
	18	1800	1900			
	20	2000	2100			

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COMPLIANT

## **VS-ST300C Series**



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ABSOLUTE MAXIMUM RATING		-	TEOT CON		VALUES	
PARAMETER	SYMBOL		TEST CON	IDITIONS	VALUES	UNITS
Maximum average on-state current	l=	180° condu	ction, half sine v	vave	650 (320)	А
at heatsink temperature	I <sub>T(AV)</sub>	double side (single side) cooled		55 (75)	°C	
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 25 °C	heatsink tempe	erature double side cooled	1290	
		t = 10 ms	No voltage		8000	
Maximum peak, one-cycle non-repetitive surge current		t = 8.3 ms	reapplied		8380	A kA <sup>2</sup> s
	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>BBM</sub>	Sinusoidal half wave, initial T <sub>J</sub> = T <sub>J</sub> maximum	6730	
		t = 8.3 ms	reapplied		7040	
Marian Patantain	l <sup>2</sup> t	t = 10 ms	No voltage reapplied		320	
		t = 8.3 ms			292	
Maximum I <sup>2</sup> t for fusing		t = 10 ms	100 % V <sub>RRM</sub>		226	
		t = 8.3 ms	reapplied		207	
Maximum I²√t for fusing	l²√t	t = 0.1 to 10	ms, no voltage	reapplied	3200	kA²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$ ), $T_J = T_J$ maximum	0.97	v
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	), T <sub>J</sub> = T <sub>J</sub> maxin	num	0.98	
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$ ), $T_J = T_J$ maximum	0.74	
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J maximum$		0.73	mΩ	
Maximum on-state voltage	V <sub>TM</sub>	$I_{pk} = 1635 \text{ A}, T_J = T_J \text{ maximum, } t_p = 10 \text{ ms sine pulse}$		2.18	V	
Maximum holding current	Ι <sub>Η</sub>	T 05 90	onodo oupple d		600	
Typical latching current	١L	$I_{\rm J} = 25 {}^{\circ}{\rm C},$	anode supply 1	2 V resistive load	1000	mA

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega,t_r \leq 1~\mu s$ $T_J$ = $T_J$ maximum, anode voltage $\leq 80~\%~V_{DRM}$	1000	A/µs		
Typical delay time	t <sub>d</sub>	Gate current 1 A, dl <sub>g</sub> /dt = 1 A/ $\mu$ s V <sub>d</sub> = 0.67 % V <sub>DRM</sub> , T <sub>J</sub> = 25 °C	1.0			
Typical turn-off time	tq	$I_{TM}$ = 300 A, $T_J$ = $T_J$ maximum, dl/dt = 40 A/µs, $V_R$ = 50 V, dV/dt = 20 V/µs, gate 0 V 100 $\Omega,$ $t_p$ = 500 µs	100	μs		

BLOCKING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J maximum linear to 80 \% rated V_{DRM}$	500	V/µs		
Maximum peak reverse and off-state leakage current	I <sub>RRM,</sub> I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	50	mA		



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TRIGGERING						
PARAMETER	SYMBOL				UES	UNITS
PARAMETER	STINDUL	12	ST CONDITIONS	TYP.	MAX.	
Maximum peak gate power	P <sub>GM</sub>	$T_J = T_J$ maximum,	t <sub>p</sub> ≤ 5 ms	1(	0.0	w
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	vv
Maximum peak positive gate current	I <sub>GM</sub>	$T_J = T_J$ maximum,	t <sub>p</sub> ≤ 5 ms	3	.0	А
Maximum peak positive gate voltage	+ V <sub>GM</sub>		t < 5 mg	2	20	v
Maximum peak negative gate voltage	- V <sub>GM</sub>	$T_J = T_J$ maximum, $t_p \le 5$ ms		5.0		]
		T <sub>J</sub> = - 40 °C		200	-	
DC gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units	100	200	mA
		T <sub>J</sub> = 125 °C		50	-	
		T <sub>J</sub> = - 40 °C		2.5	-	
DC gate voltage required to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C	12 V anode to cathode applied	1.8	3.0	V
		T <sub>J</sub> = 125 °C			-	
DC gate current not to trigger	I <sub>GD</sub>	Maximum gate current/voltage not to trigger is the maximum		10	0.0	mA
DC gate voltage not to trigger	V <sub>GD</sub>	ij=ij maximum	= T <sub>J</sub> maximum value which will not trigger any - unit with rated V <sub>DRM</sub> anode to cathode applied		25	v

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction temperature range	TJ		- 40 to 125	°C	
Maximum storage temperature range	T <sub>Stg</sub>		- 40 to 150	C	
Maximum thermal registance, junction to heataink	Р	DC operation single side cooled	0.09		
Maximum thermal resistance, junction to heatsink	R <sub>thJ-hs</sub>	DC operation double side cooled	0.04	K/W	
Maximum thermal resistance, case to heatsink	R <sub>thC-hs</sub>	DC operation single side cooled	0.02		
		DC operation double side cooled	0.01		
Mounting force, ± 10 %			9800 (1000)	N (kg)	
Approximate weight			83	g	
Case style		See dimensions - link at the end of datasheet	E-PUK (TO-	200AB)	

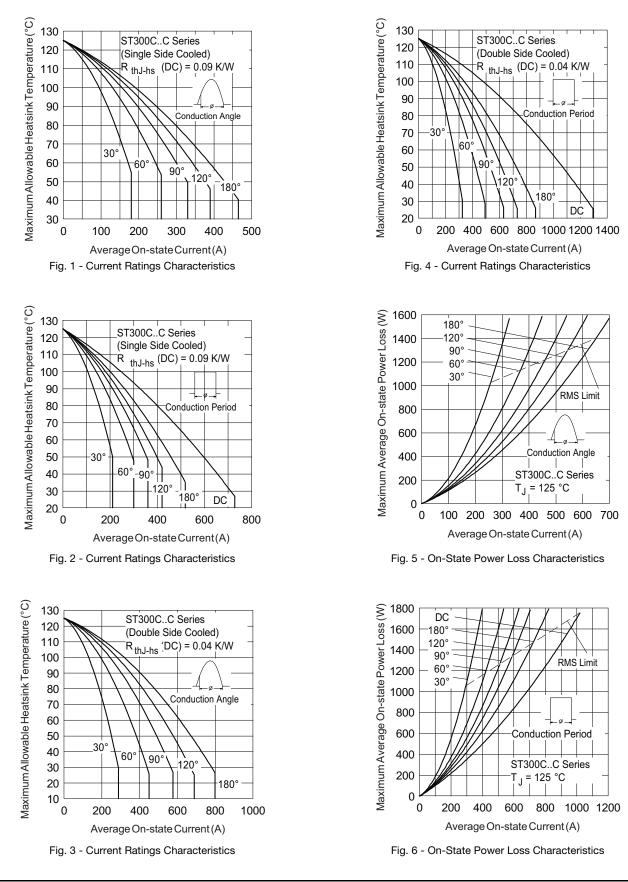
CONDUCTION ANGLE	SINUSOIDAL	CONDUCTION	RECTANGULA	R CONDUCTION		UNITS	
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS	
180°	0.010	0.011	0.007	0.007			
120°	0.012	0.012	0.012	0.013			
90°	0.015	0.015	0.016	0.017	$T_J = T_J maximum$	K/W	
60°	0.022	0.022	0.023	0.023			
30°	0.036	0.036	0.036	0.037			

Note

• The table above shows the increment of thermal resistance RthJ-hs when devices operate at different conduction angles than DC

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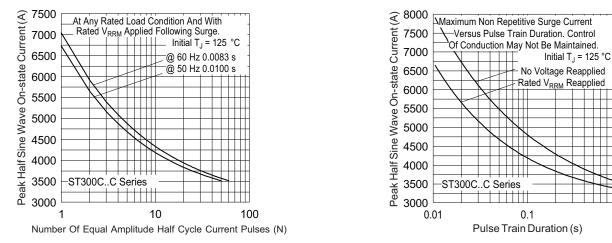
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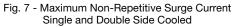
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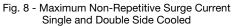
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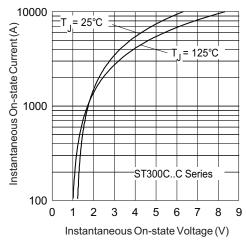
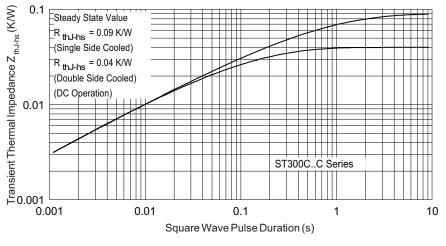
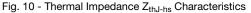


Fig. 9 - On-State Voltage Drop Characteristcs

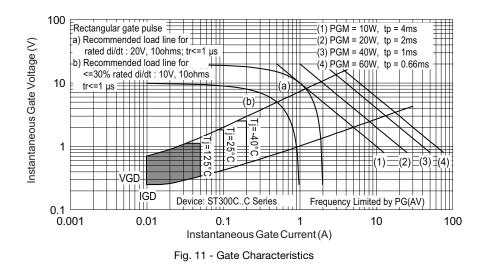




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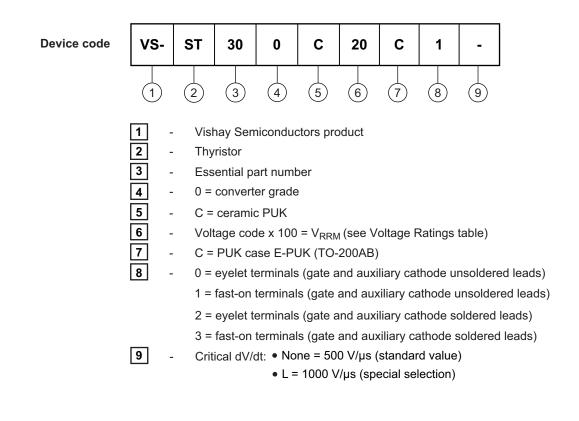
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LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95075		

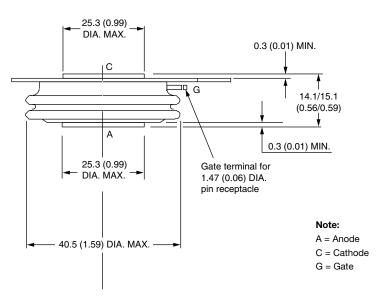




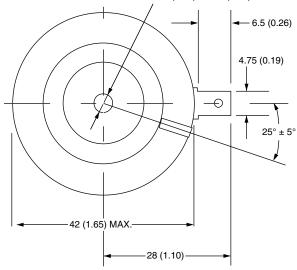
## E-PUK (TO-200AB)

#### **DIMENSIONS** in millimeters (inches)

Anode to gate Creepage distance: 11.18 (0.44) minimum Strike distance: 7.62 (0.30) minimum



2 holes 3.56 (0.14) x 1.83 (0.07) minimum deep



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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